a2 cont.

wherein the first thickness is between about 0.5 and about 33 percent and the second thickness is between about 0.5 and about 33 percent of the sum of the first, second and third thicknesses.

Please amend Claim 2 to recite as follows:

2. (Amended) A capacitor having a dielectric structure comprising:

a silicon carbide layer;

a first oxide layer having a first thickness on the silicon carbide layer;

a layer of dielectric material on the first oxide layer and having a second thickness, the layer of dielectric material having a dielectric constant higher than the dielectric constant of the first oxide layer;

a second oxide layer on the layer of dielectric material opposite the first oxide layer and having a third thickness;

wherein the first thickness is between about 0.5 and about 33 percent and the second thickness is between about 0.5 and about 33 percent of the sum of the first, second and third thicknesses;

a first metal layer on the first oxide layer opposite the layer of dielectric material and disposed between the first oxide layer and the silicon carbide layer; and

a second metal layer on the second oxide layer opposite the high dielectric layer so as to provide a metal-insulator-metal (MIM) capacitor.

Please cancel Claim 32.

Please amend Claim 33 to recite as follows:

a3

33 → 22. (Amended) A capacitor comprising:

a silicon carbide layer;

a layer of dielectric material on the silicon carbide layer, the layer of dielectric material comprising silicon oxynitride having a formula $Si_3N_{4-X}O_X$, where $0<X<1$;

a first metal layer on the layer of dielectric material opposite the silicon carbide layer; and

a second metal layer on the layer of dielectric material and disposed between the layer of dielectric material and the silicon carbide layer so as to provide a metal-insulator-metal (MIM) capacitor.